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- M. Dammann, M. Chertouk, W. Jantz, K. Köhler and G. Weimann 1711 Reliability of InAlAs/InGaAs HEMTs grown on GaAs substrate with metamorphic buffer
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- R. Petersen, W. De Ceuninck, L. De Schepper and J-L. Muraro 1723 A method to minimize test time for accelerated ageing of pHEMT's by analysis of the electronic fingerprint of the initial stage of degradation
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- M. Vanzi, G. Salmini and R. De Palo 1755 New FIB/TEM evidence for a REDR mechanism in sudden failures of 980 nm SL SQW InGaAs/AlGaAs pump laser diodes
- R. Desplats, T. Dargnies, J.-C. Courrege, P. Perdu and J.-L. Noullet 1761 Calculation of the optimal FIB milling and deposition operations for easier and faster circuit reconfiguration
- N. Mattern, M. Hecker, D. Fischer, C. Wenzel, N. Schell, W. Matz, H. Engelmann and E. Zschech 1767 X-ray structure characterization of barriers for Cu metallization

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- C. Claeys and E. Simoen** 1815 *Invited Paper*
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- E. P. Vandamme and L. K. J. Vandamme** 1847 *Invited Paper*
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- M. J. Deen and S. Romyantsev** 1855 *Invited Paper*
Low frequency noise in complementary npn and pnp polysilicon emitter bipolar junction transistors
- M. Sandén, B. G. Malm, J. V. Grahn and M. Östling** 1863 Decreased low frequency noise by hydrogen passivation of polysilicon emitter bipolar transistors
- C. Delseny, A. Pénarier, F. Pascal, S. G. Jarrix and P. Llinares** 1869 Comparison of low frequency noise and high frequency performances of double and simple polysilicon Bi-CMOS BJT
- N. V. Amarasinghe, Z. Çelik-Butler and P. Vasina** 1875 Characterization of oxide traps in $0.15 \mu\text{m}^2$ MOSFETs using random telegraph signals
- F.-C. Hou, G. Bosman and M. E. Law** 1883 Characterization of generation-recombination noise using a physics-based device noise simulator
- D. Pogany, E. Gornik, M. Stecher and W. Werner** 1887 Random telegraph noise and leakage current in smart power technology DMOS devices
- A. Mercha, J. Rhayem, L. Pichon, M. Valenza, J. M. Routoure, R. Carin, O. Bonnaud and D. Rigaud** 1891 Low-frequency noise in low temperature *unhydrogenated* polysilicon thin film transistors

IV. COMPOUND DEVICES

- J. A. Chroboczek and G. Ghibaudo** 1897 *Invited Paper*
Low frequency noise in SiGe-base heterojunction bipolar transistors and SiGe-channel metal oxide semiconductor field effect transistors
- C. Surya, C. F. Zhu, B. H. Leung, W. K. Fong, C. C. Cheng and J. K. O. Sin** 1905 *Invited Paper*
Study of the effects of rapid thermal annealing in generation-recombination noise in MBE grown GaN thin films

- Invited Paper*
- J. Berntgen, A. Behres, J. Kluth, K. Heime, W. Daumann, U. Auer and F.-J. Tegude 1911 Hooe parameter of InGaAs bulk material and InGaAs 2DEG quantum well structures based on InP substrates
- J. C. Vildeuil, M. Valenza and D. Rigaud 1915 Low frequency noise in gate and drain of PHEMT's and related correlation
- M. Tacano, M. Ando, I. Shibasaki, S. Hashiguchi, J. Sikula and T. Matsui 1921 Dependence of Hooe parameter of InAs heterostructure on temperature
- X. Y. Chen, A. Pedersen, O. G. Hellesø and A. D. van Rheeën 1925 Electrical noise of laser diodes measured over a wide range of bias currents
- F. Principato and G. Ferrante 1929 Experimental determination of the kurtosis of RF noise in microwave low-noise devices

V. SYSTEMS AND INTERCONNECTION

- E. F. Tsakas and A. N. Birbas 1937 Noise optimisation for the design of a reliable high speed X-ray readout integrated circuit
- K. Takagi, S. Serikawa and A. Okuno 1943 $1/f$ phase noise in a transistor and its application to reduce the frequency fluctuation in an oscillator
- T. González, J. Mateos, D. Pardo, O. M. Bulashenko and L. Reggiani 1951 Effect of dimensionality on shot-noise suppression in nondegenerate diffusive conductors
- S. Di Pascoli and G. Iannaccone 1955 Simulation of electromigration noise in polycrystalline metal stripes

VI. MISCELLANEOUS

- O. Marinov 1959 The low frequency noise in HFETs estimates the effect of electrical stress
- A. Godoy, J. A. Jiménez-Tejada, A. Palma and J. E. Carceller 1965 Optimum design in a JFET for minimum generation-recombination noise
- F. Principato and G. Ferrante 1969 Skewness and kurtosis of $1/f$ noise in semiconductor devices
- J. Briare and L. K. J. Vandamme 1975 The influence of a digital spectrum analyzer on the uncertainty in $1/f$ noise parameters

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- Introductory Invited Papers*
- K. P. Cheung 1981 Plasma-charging damage in ultra-thin gate oxide
- Y. Wu, Q. Xiang, J. Y. M. Yang, G. Lucovsky and M.-R. Lin 1987 Time-dependent dielectric wearout technique with temperature effect for reliability test of ultrathin (<2.0 nm) single layer and dual layer gate oxides
- V. V. Belyakov, A. I. Chumakov, A. Y. Nikiforov, V. S. Pershenkov, P. K. Skorobogatov and A. V. Sogoyan 1997 IC's radiation effects modeling and estimation
- Research Papers*
- C. Lee, J.-S. Kim, H. Shin, Y.-J. Park and H.-S. Min 2019 A new hole mobility model for hydrodynamic simulation
- A. A. Tarasenko, F. Nieto, L. Jastrabík and C. Uebing 2023 The influence of adatom diffusion on coverage and emission current fluctuations
- A. Paskaleva and E. Atanassova 2033 Bulk oxide charge and slow states in Si-SiO₂ structures generated by RIE-mode plasma
- B.-Y. Tsui, S.-S. Lin, C.-S. Tsai and C. C. Hsia 2039 Plasma charging damage during contact hole etch in high-density plasma etcher

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